

FDS4935A

Dual 30V P-Channel PowerTrench® MOSFET

General Description

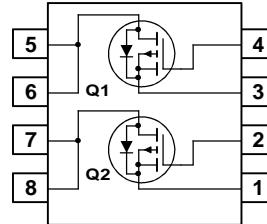
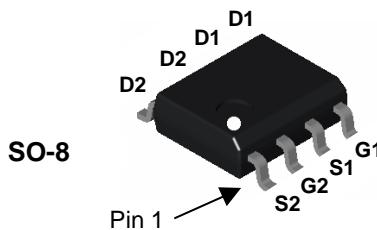
This P-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V – 20V).

Applications

- Power management
- Load switch
- Battery protection

Features

- $-7\text{ A}, -30\text{ V}$ $R_{DS(ON)} = 23\text{ m}\Omega @ V_{GS} = -10\text{ V}$
 $R_{DS(ON)} = 35\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- Low gate charge (15nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous	-7	A
	– Pulsed		
P_D	Power Dissipation for Dual Operation	2	W
P_D	Power Dissipation for Single Operation	1.6	
		1	
		0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

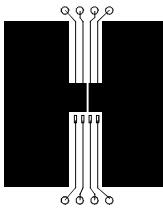
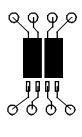
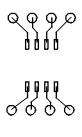
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS4935A	FDS4935A	13"	12mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units		
Off Characteristics								
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$	-30			V		
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		-24		$\text{mV/}^\circ\text{C}$		
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}$, $V_{GS} = 0 \text{ V}$			-10	μA		
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = -20 \text{ V}$, $V_{DS} = 0 \text{ V}$			-100	nA		
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			100	nA		
On Characteristics (Note 2)								
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-1	-1.6	-3	V		
$\Delta V_{GS(\text{th})}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		4.4		$\text{mV/}^\circ\text{C}$		
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}$, $I_D = -7 \text{ A}$ $V_{GS} = -4.5 \text{ V}$, $I_D = -5.5 \text{ A}$ $V_{GS} = -10 \text{ V}$, $I_D = -7 \text{ A}$, $T_J = 125^\circ\text{C}$		19 28 26	23 35 34	$\text{m}\Omega$		
$I_{D(\text{on})}$	On-State Drain Current	$V_{GS} = -10 \text{ V}$, $V_{DS} = -5 \text{ V}$	-30			A		
g_{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}$, $I_D = -7 \text{ A}$		19		S		
Dynamic Characteristics								
C_{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$		1233		pF		
C_{oss}	Output Capacitance			311		pF		
C_{rss}	Reverse Transfer Capacitance			152		pF		
Switching Characteristics (Note 2)								
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = -15 \text{ V}$, $I_D = -1 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_{\text{GEN}} = 6 \Omega$		13	23	ns		
t_r	Turn-On Rise Time			10	20	ns		
$t_{d(\text{off})}$	Turn-Off Delay Time			48	77	ns		
t_f	Turn-Off Fall Time			25	40	ns		
Q_g	Total Gate Charge	$V_{DS} = -15 \text{ V}$, $I_D = -7 \text{ A}$, $V_{GS} = -5 \text{ V}$		15	21	nC		
Q_{gs}	Gate-Source Charge			4.4		nC		
Q_{gd}	Gate-Drain Charge			4.5		nC		
Drain-Source Diode Characteristics and Maximum Ratings								
I_S	Maximum Continuous Drain-Source Diode Forward Current				-2.1	A		
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = -2.1 \text{ A}$ (Note 2)		-0.75	-1.2	V		
Notes:								
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.								
		a) 78°C/W when mounted on a 0.5in^2 pad of 2 oz copper			b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz copper			c) 135°C/W when mounted on a minimum pad.
Scale 1 : 1 on letter size paper								
2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%								

Typical Characteristics

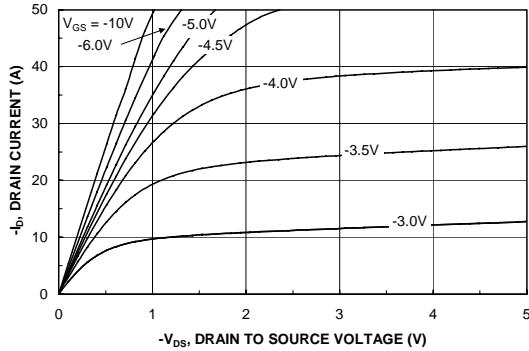


Figure 1. On-Region Characteristics.

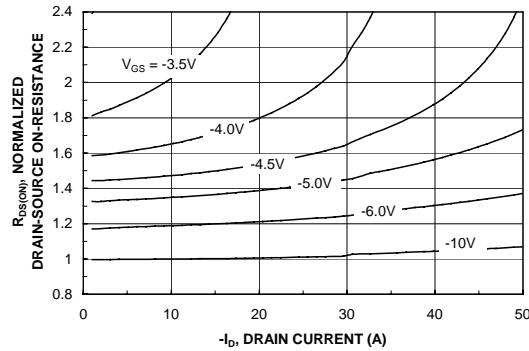


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

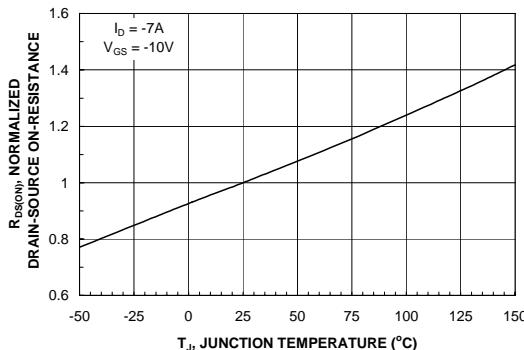


Figure 3. On-Resistance Variation with Temperature.

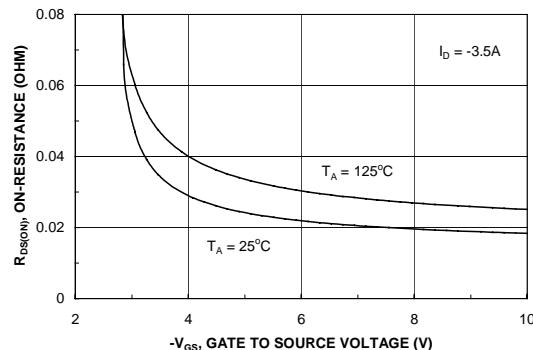


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

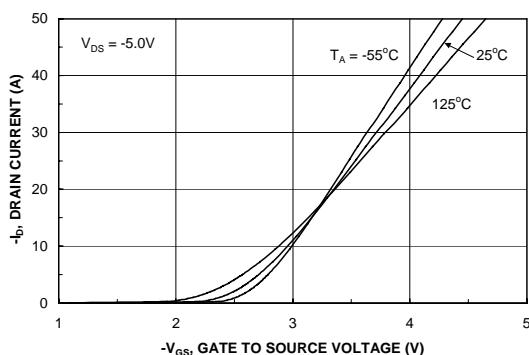


Figure 5. Transfer Characteristics.

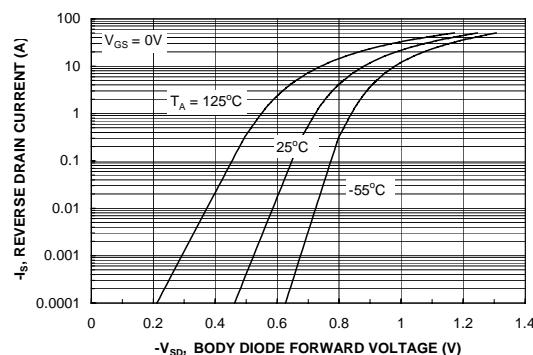


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

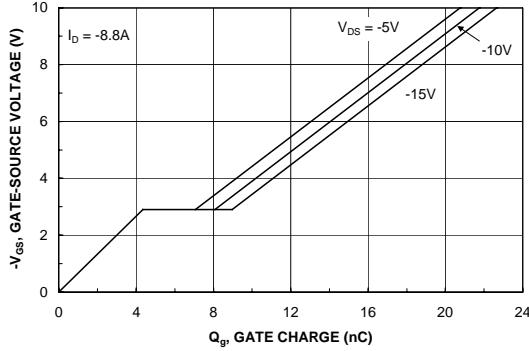


Figure 7. Gate Charge Characteristics.

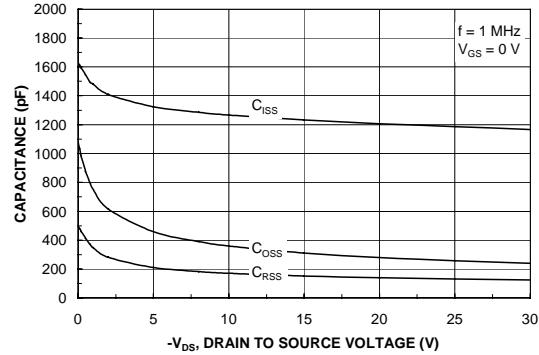


Figure 8. Capacitance Characteristics.

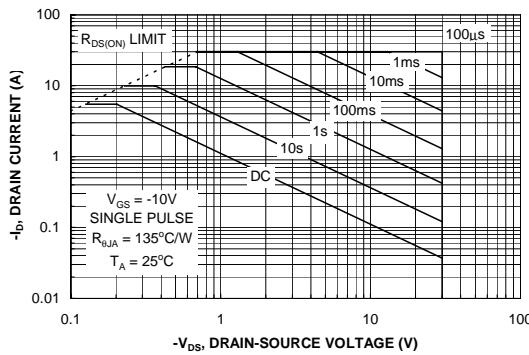


Figure 9. Maximum Safe Operating Area.

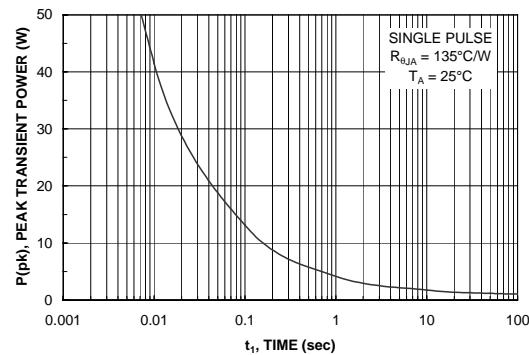


Figure 10. Single Pulse Maximum Power Dissipation.

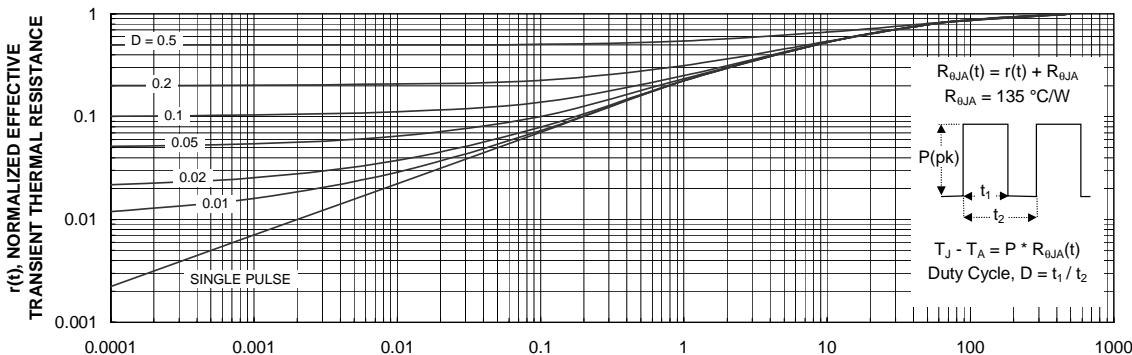


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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